

### General Description

The SM8166x high efficiency synchronous buck converter operates over a wide input voltage range of 4.5V to 18V, and can deliver an output current up to 6A. It integrates a top MOSFET and a bottom MOSFET with very low  $R_{DS(ON)}$  to minimize conduction loss. The 400kHz/1000kHz pseudo-constant switching frequency enables using small external inductor and capacitor values.

The SM8166x uses constant on-time and ripple-based control strategy to achieve fast transient response for applications with high step-down ratios, and high efficiency at light loads. It also provides cycle-by-cycle current limit protection, output under voltage protection and over temperature protection.

Only the input and output capacitors, inductor, feedback resistor divider and feedforward capacitor need to be selected for the targeted application specifications.

The SM8166x is available in a compact TSOT23-6 and TSOT23-8 package. The device is part of a family which shares the same package and pinout. The details are shown below.

Part Number	Package	Frequency	Light Load Operation Mode
SM8166ADT	TSOT23-6	400kHz	PFM
SM8166EADT			FCCM
SM8166CADT		1000kHz	PFM
SM8166BADT			FCCM
SM8166AIT	TSOT23-8	400kHz	PFM
SM8166EAIT			FCCM
SM8166CAIT		1000kHz	PFM
SM8166BAIT			FCCM

### Features

- Low  $R_{DS(ON)}$  for Internal MOSFETs: 35mΩ Top, 23mΩ Bottom
- Wide Input Voltage Range: 4.5V ~ 18V
- Adjustable Output Voltage: 0.6V ~ 9.5V
- Up to 6A Output Current
- $\pm 1\%$  0.6V Reference
- Precise EN Threshold
- Pulse-Frequency Modulation (PFM) Mode Operation for SM8166 and SM8166C
- Forced Continuous Conduction Mode (FCCM) Operation for SM8166E and SM8166B
- Internal Soft-Start Limits the Inrush Current
- Support Smooth Startup with Pre-Biased Output
- 400kHz/1000kHz Switching Frequency Minimizes the External Components
- Constant On-time and Ripple-Based Control to Achieve Fast Transient Responses
- Optional Adjustable Soft-Start and Power Good Indicator Function (TSOT23-8)
- Output Auto-Discharge Function
- Cycle-by-Cycle Valley and Peak Current Limit Protection
- Hic-Cup Mode Output Under Voltage Protection
- Auto-Recovery Mode Over Temperature Protection
- Input Under Voltage Lockout (UVLO)
- RoHS-Compliant and Halogen-Free
- Compact Package: TSOT23-6/TSOT23-8

### Applications

- Set-Top Box
- Portable TV
- DSL Modem
- LCD TV
- IP Camera
- Network

### Typical Application

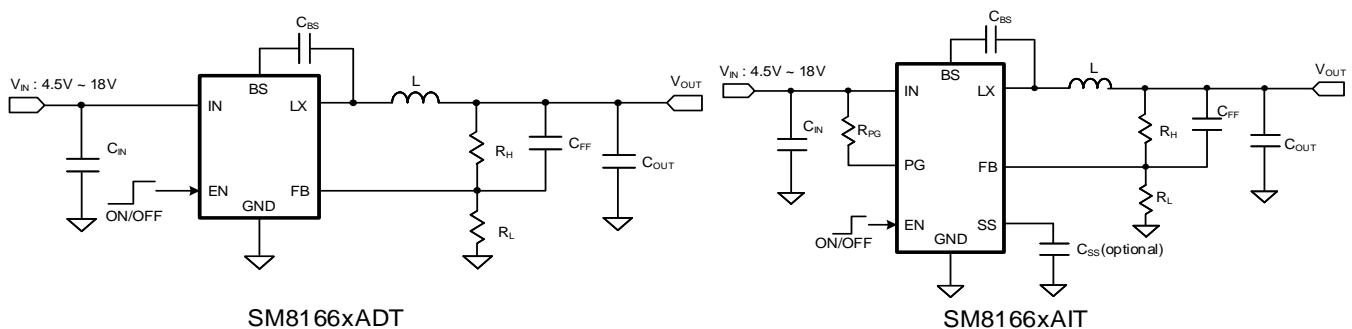


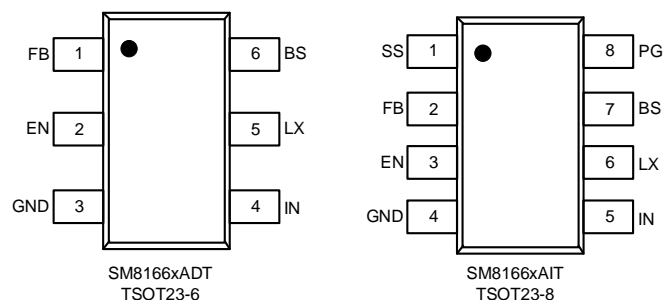
Figure 1. Schematic Diagram

## Ordering Information

Ordering Part Number	Package type	Top Mark
SM8166ADT	TSOT23-6 RoHS Compliant and Halogen Free	<b>LBB</b> xyz
SM8166EADT		<b>LBC</b> xyz
SM8166CADT		<b>LBD</b> xyz
SM8166BADT		<b>LBE</b> xyz
SM8166AIT	TSOT23-8 RoHS Compliant and Halogen Free	<b>LBF</b> xyz
SM8166EAIT		<b>LBG</b> xyz
SM8166CAIT		<b>LBH</b> xyz
SM8166BAIT		<b>LBJ</b> xyz

*x = year code, y = week code, z = lot number code*

## Pinout (top view)



## Pin Description

Pin Name	Pin No		Pin Description
	SM8166xADT	SM8166xAIT	
SS	/	1	Soft-start time programming pin. Connect a capacitor from this pin to ground to program the soft-start time. $t_{SS} = C_{SS} \times 0.6V / I_{SS}$ . Leave this pin open for default minimum soft-start time.
FB	1	2	Output feedback pin. Connect this pin to the center point of the output resistor divider as shown in Figure 1. $V_{OUT} = 0.6V \times (1 + R_H/R_L)$ .
EN	2	3	Enable control pin. Pull this pin higher than EN rising threshold to turn on the device and pull this pin lower than EN falling threshold to turn off the device. Do not leave this pin floating.
GND	3	4	Ground pin.
IN	4	5	Input pin. Decouple this pin to GND pin with at least a 10 $\mu$ F ceramic capacitor.
LX	5	6	Inductor pin. Connect this pin to the switching node of inductor.
BS	6	7	Bootstrap pin. Supply top FET gate driver. Connect a 0.1 $\mu$ F ceramic capacitor between BS and LX pin.
PG	/	8	Power good indicator pin. PG pin should be connected to VIN or another voltage source through a resistor (e.g., 10k $\Omega$ ~ 100k $\Omega$ ). This pin becomes high when the output voltage is within 90% to 120% of regulated value under normal operation.

## Block Diagram

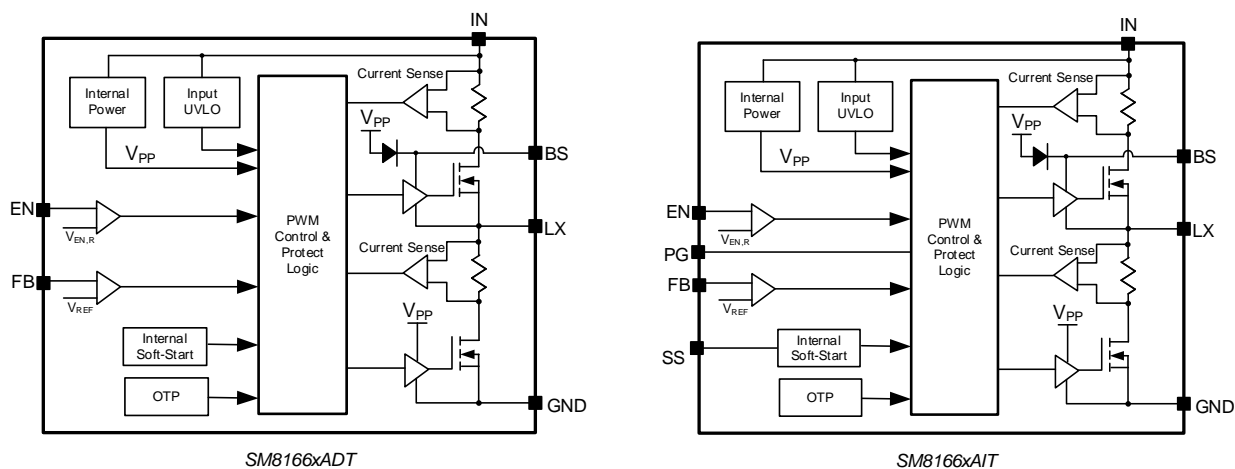


Figure2. Block Diagram

## Absolute Maximum Ratings

Parameter (Note 1)	Min	Max	Unit
IN	-0.3	19	V
EN, LX, PG	-0.3	IN + 0.3	
BS-LX, FB, SS	-0.3	4	
LX, 10ns duration	- 5	IN + 3	
LX, 20ns duration	- 1	IN + 2	
Junction Temperature, Operating	-40	150	°C
Lead Temperature (Soldering, 10s)		260	
Storage Temperature	-65	150	

## Thermal Information

Parameter (Note 2)	Typ		Unit
	TSOT23-6	TSOT23-8	
$\theta_{JA}$ Junction-to-Ambient Thermal Resistance	TBD	TBD	°C/W
$\theta_{JC}$ Junction-to-Case Thermal Resistance	TBD	TBD	°C/W
$P_D$ Power Dissipation $T_A = 25^\circ\text{C}$	TBD	TBD	W

## Recommended Operating Conditions

Parameter (Note 3)	Min	Max	Unit
Input Voltage	4.5	18	V
Output Voltage	0.6	9.5	
Continuous Output Current		6	A
Ambient Temperature	-40	85	°C
Junction Temperature	-40	125	

## Electrical Characteristics

( $V_{IN} = 12V$ ,  $V_{OUT} = 3.3V$ ,  $L = 3.3\mu H$ ,  $C_{OUT} = 32\mu F$ ,  $T_J = 25^\circ C$ ,  $I_{OUT} = 1A$  unless otherwise specified(Note 4))

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit		
Input	Voltage Range	$V_{IN}$	4.5		18	V		
	UVLO Rising Threshold	$V_{IN,UVLO}$	$V_{IN}$ rising		4.45			
	UVLO Hysteresis	$V_{IN,HYS}$		0.3				
	Quiescent Current	$I_Q$	$I_{OUT} = 0A$ , $V_{FB} = V_{REF} \times 105\%$		200	$\mu A$		
	Shutdown Current	$I_{SHDN}$	$V_{EN} = 0V$		5		10	
Output	Voltage Range	$V_{SET}$	0.6		9.5	V		
	FB Reference Voltage	$V_{REF}$	594	600	606	mV		
	FB Input Current	$I_{FB}$	$V_{FB} = 1V$	-50		50	nA	
	Discharge FET Resistance	$R_{DIS}$			50	$\Omega$		
	Turn On Delay	$t_{ON,DLY}$	From EN high to LX starts switching (Note 5)		0.5		ms	
	Soft-Start Time	$t_{SS}$	$V_{OUT}$ from 0% to 100% $V_{SET}$ (SM8166xADT)		1.7			
	Minimum Soft-Start Time	$t_{SS,MIN}$	Without $C_{SS}$ , $V_{OUT}$ from 0% to 100% $V_{SET}$ (SM8166xAIT)		1.7			
	SS Charging Current	$I_{SS}$	(SM8166xAIT)		7.3			$\mu A$
	UVP Threshold	$V_{UVP}$			33			$\%V_{REF}$
	UVP Delay	$t_{UVP,DLY}$			100		$\mu s$	
	UVP Hiccup On-Time	$t_{HICCUP,ON}$			x		ms	
	UVP Hiccup Off-Time	$t_{HICCUP,OFF}$			3x			
Enable (EN)	Rising Threshold	$V_{EN,R}$	1.08	1.2	1.32	V		
	Falling Threshold	$V_{EN,F}$	0.9	1.0	1.1			
	De-Glitch Time	$t_{EN,DG}$		4		$\mu s$		
	Input Current	$I_{EN}$	$V_{EN} = 0V \sim V_{IN}$		0		$\mu A$	
MOSFET	Top MOSFET $R_{DS(ON)}$	$R_{DS(ON),TOP}$		35		m $\Omega$		
	Bottom MOSFET $R_{DS(ON)}$	$R_{DS(ON),BOT}$		23				
	Top MOSFET Current Limit Threshold	$I_{LMT,TOP}$		8		A		
	Bottom MOSFET Current Limit Threshold	$I_{LMT,BOT}$		6.5				
Power Good (SM8166xAIT)	Rising Threshold	$V_{PG,R}$	$V_{FB}$ rising (good)	87	92	97	$\%V_{REF}$	
	Falling Threshold	$V_{PG,F}$	$V_{FB}$ falling (not good)	82	87	92		
	OVP Threshold	$V_{PG,OVP}$	$V_{FB}$ rising (not good)	115	120	125		
	OVP Recovery Threshold	$V_{PG,REC}$	$V_{FB}$ falling (good)	102	107	112	$\mu s$	
	OVP Delay	$t_{OVP,DLY}$			40			
	Delay Time	$t_{PG,R}$	$V_{EN} = 3.3V$ , low to high		50			
		$t_{PG,F}$	$V_{EN} = 3.3V$ , high to low		35			
		$t_{PG,OFF}$	IC shuts down from $V_{IN}$ , EN and OTP			1		
Leakage Current	$I_{PG,LOW}$	$V_{FB} = V_{REF}$ , PG adds 3.3V		0	3	$\mu A$		
Low Voltage	$V_{PG,LOW}$	$V_{FB} = 0V$ , $I_{PG} = 5mA$			0.4	V		



# SM8166/SM8166E/SM8166C/SM8166B

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Frequency	Switching Frequency	$f_{sw}$	$I_{OUT} = 1A, CCM$		400		kHz
	Minimum On-Time	$t_{ON,MIN}$			50		ns
	Minimum Off-Time	$t_{OFF,MIN}$			150		
OTP	Temperature	$T_{OTP}$	(Note 5)		150		°C
	Temperature Hysteresis	$T_{HYS}$	(Note 5)		15		

**Note 1:** Stresses beyond the “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Note 2:**  $\theta_{JA}$  is measured in the natural convection at  $T_A = 25^\circ C$  on a 6cmx6cm size, four-layer Silergy Evaluation Board with 2-oz copper. Case temperature  $\theta_{JC}$  is measured at LX pin.

**Note 3:** The device is not guaranteed to function outside its operating conditions.

**Note 4:** Unless otherwise stated, limits are 100% production tested under pulsed load conditions such that  $T_A \cong T_J = 25^\circ C$ . Limits over the operating temperature range (See recommended operating conditions) and relevant voltage range(s) are guaranteed by design, test, or statistical correlation.

**Note 5:** Guaranteed by design or statistical correlation and not production tested.

## Detailed Description

### General Description

The SM8166x high efficiency synchronous buck converter operates over a wide input voltage range of 4.5V to 18V, and can deliver an output current up to 6A. It integrates a top MOSFET and a bottom MOSFET with very low  $R_{DS(ON)}$  to minimize conduction loss. The 400kHz/1000kHz pseudo-constant switching frequency allows small external inductor and capacitor values.

The SM8166x also provides cycle-by-cycle current limit protection output under voltage protection and over temperature protection.

### Constant On-Time and Ripple-Based Control Strategy

The device uses instant PWM architecture to achieve fast transient response for applications with high step-down ratios, and high efficiency at light loads. It uses a constant on-time and ripple-based control strategy in which a virtual replica of the inductor current signal is synthesized internally and combined with the feedback voltage. When the sum voltage is lower than the reference voltage, the bottom MOSFET turns off and the top MOSFET turns on for a fixed period of time (Constant  $t_{ON}$ ).  $t_{ON}$  is internally calculated according to the input voltage, output voltage, and desired switching frequency ( $f_{SW}$ ):

$$t_{ON} = \frac{V_{OUT}/V_{IN}}{f_{SW}}$$

The top MOSFET turns off after a period of  $t_{ON}$ .

### Minimum Duty Cycle and Maximum Duty Cycle

In the COT architecture, there is no limitation for low duty cycle operation, because the switching frequency can be reduced as needed to always ensure proper operation when the on-time is close to the minimum on time.

The SM8166 and SM8166E can support a maximum duty cycle of up to 80% across the entire operating temperature range of  $-40^{\circ}\text{C} \sim 125^{\circ}\text{C}$ .

The SM8166B and SM8166C can support a maximum duty cycle of up to 70% across the entire operating temperature range of  $-40^{\circ}\text{C} \sim 125^{\circ}\text{C}$ .

### PFM Light Load Operation

The SM8166 and SM8166C use pulse-frequency modulation (PFM) operation mode under light load condition for high efficiency. Under light load conditions, typically when the load satisfies the following equation,

$$I_{OUT\_CTL} = \frac{\Delta I_L}{2} = \frac{V_{OUT} \times (1 - D)}{2 \times f_{SW} \times L} \quad (1)$$

the current through the bottom MOSFET will ramp to near zero before the next  $t_{ON}$  time. When this occurs, the bottom

MOSFET turns off, preventing recirculation current that can seriously reduce efficiency under these light load conditions. As load current is further reduced, the combined feedback and ramp signals remain much higher than the reference voltage, the instant-PWM control loop will not trigger another  $t_{ON}$  until needed, and the apparent operating switching frequency will correspondingly drop, improving efficiency. Continuous conduction mode (CCM) resumes smoothly as soon as the load current increases sufficiently for the inductor current to remain above zero at the time of the next  $t_{ON}$  cycle. The buck converter enters CCM once the load current exceeds the threshold shown in (1). Above the threshold, the switching frequency stays fairly constant over the output current range.

While in PFM mode, the output of the device doesn't require over voltage protection because the device stops switching as soon as the voltage at the FB node increases above  $V_{REF}$ , preventing the output voltage from increasing further.

### FCCM Light Load Operation

SM8166E and SM8166B use forced continuous conduction mode (FCCM) under light load condition. Under light load conditions, the bottom MOSFET still turns on even when the inductor current crosses zero. Current flow will continue until the next  $t_{ON}$  cycle. The device always operates under continuous conditions mode and keeps fairly constant switching frequency over all the output current range.

### Input Under Voltage Lockout (UVLO)

To prevent operation before all internal circuitry is ready and to ensure that the top MOSFET and bottom MOSFET can be correctly biased, the device incorporates input under voltage lockout protection. The device remains in a low current state and all LX node switching actions are inhibited until  $V_{IN}$  exceeds its rising threshold. At that time, if EN is enabled, the device will startup. If  $V_{IN}$  falls below  $V_{IN,UVLO}$  less than the input UVLO hysteresis, the LX node switching actions will again be suppressed.

### Precise EN Threshold

The EN pin uses precise rising and falling thresholds to provide programmable ON/OFF control. The device will be turned on when the EN pin voltage exceeds the rising threshold. The device will be turned off while the EN pin voltage falls below the falling threshold. Increasing the UVLO startup voltage threshold is possible using an external resistor divider as shown below:

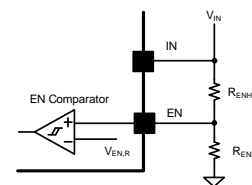


Figure4. EN Control

It is not recommended to connect EN pin to the  $V_{IN}$  or another voltage source directly. A resistor with a value between  $1k\Omega$  and  $1M\Omega$  is recommended if the EN pin is pulled high.

### Soft-Start and Startup with Pre-Biased Output

The device incorporates an internal soft-start circuit to ramp the output to the desired voltage whenever the device is enabled. Internally, the soft-start circuit clamps the output at a low voltage and then allows the output to rise to the desired voltage over approximately 1ms, which avoids high current flow and transients during startup.

The device supports startup with pre-biased output. If the output is pre-biased to a certain voltage before startup, the buck converter disables the switching of both the top MOSFET and the bottom MOSFET until the internal soft-start voltage  $V_{SS}$  exceeds the sensed output voltage at the FB node. The first pulse on-time is internally calculated based the input voltage and pre-biased output voltage.

### Output Auto-Discharge Function

The device discharges the output voltage when the buck converter shuts down due to low  $V_{IN}$  or EN, or caused by over temperature protection, so that the output voltage can be discharged in a minimal time, even if the buck output load current is zero. The discharge MOSFET in parallel with the bottom MOSFET turns on after the bottom MOSFET turns off when the shutdown logic is enabled. The output discharge MOSFET resistance is  $50\Omega$ . The discharge MOSFET is not active outside of these shutdown conditions.

### External Bootstrap Capacitor

The external bootstrap capacitor provides the gate driver voltage for the N-channel top MOSFET. A  $0.1\mu F$  low ESR ceramic capacitor connected between the BS pin and the LX pin is recommended.

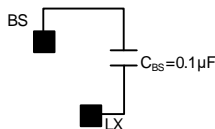


Figure5. Bootstrap Capacitor Connection

### Programmable Soft-start Time (TSOT23-8)

A soft-start circuit is incorporated to smoothly ramp the output to the desired voltage whenever the device is enabled. At startup, soft-start clamps the output at a low voltage and then ramps the output to the desired voltage over the soft-start time  $t_{SS}$ , which avoids high current flow and transients during startup. The default soft-start time is 0.2ms. Longer soft-start time can be achieved by connecting a capacitor  $C_{SS}$  from SS to GND.

$$t_{SS} = \frac{C_{SS} \times 0.6V}{I_{SS}}$$

### PG Power Good Indicator (TSOT23-8)

PG is an open drain output controlled by a window comparator connected to the feedback signal. If the voltage is higher than  $V_{PG,R}$  and less than  $V_{OVP}$  for at least the power good delay time (low to high), PG will be set to high-impedance state.

PG should be connected to  $V_{IN}$  or another voltage source through a resistor (e.g.,  $100k\Omega$ ). After  $V_{IN}$  rises until the internal initial power is ready, the PG internal MOSFET is turned on so that PG is actively driven low before output voltage is ready. After the feedback voltage  $V_{FB}$  reaches  $V_{PG,R}$ , PG is set to high-impedance state after a delay time of  $50\mu s$  (typ.). When  $V_{FB}$  drops to  $V_{PG,F}$ , or rises above  $V_{OVP}$  for the OVP delay time, PG is driven low after a delay time of  $35\mu s$  (typ.).

## Fault Protection Modes

### Cycle-by-Cycle Current Limit Protection

If the top MOSFET current exceeds the top current limit threshold, it will turn off and the bottom MOSFET will turn on. If the bottom MOSFET current exceeds the bottom current limit threshold, it will stay on until the current decreases below its current limit threshold. As a result, both inductor peak and valley currents are limited.

### Output Under Voltage Protection (UVP)

With output current increasing, as soon as the bottom MOSFET current exceeds its current limit threshold, the top MOSFET will not be allowed to turn on any more. If the load current continues to increase, the output voltage will drop. When the output voltage falls below 33% of the regulated level, the output under voltage protection will be activated and the device will operate in hiccup mode. The hiccup on-time is  $xms$ , and the hiccup off-time is  $3xms$ . If the hard short condition is removed, the device will return to normal operation.

### Over Temperature Protection (OTP)

The device includes over temperature protection (OTP) circuitry to prevent overheating due to excessive power dissipation. This will shut down the device when the junction temperature exceeds  $150^{\circ}C$ . When the junction temperature is reduced by approximately  $15^{\circ}C$ , the device will resume normal operation after a complete soft-start cycle. For continuous operation, provide adequate thermal dissipation so that the junction temperature does not exceed the OTP threshold.

## Application Information

The following paragraphs provide information on the selection of the external components needed to meet the targeted application specifications.

### Feedback Resistor Divider $R_H$ and $R_L$

Choose  $R_H$  and  $R_L$  to program the proper output voltage. A value between  $1k\Omega$  and  $1M\Omega$  is recommended for both resistors to minimize power consumption under light loads. As an example, if  $V_{OUT} = 5V$  and  $R_H$  selected value is  $100k\Omega$ ,  $R_L$  can be calculated as follows:

$$R_L = \frac{0.6}{V_{OUT} - 0.6V} \times R_H$$

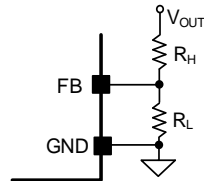


Figure6. Feedback Resistor Divider

With a calculated value of  $13.7k\Omega$  for  $R_L$ , a standard 1%  $13.7k\Omega$  resistor is selected.

### Input Capacitor $C_{IN}$

For the best performance, select a typical X5R or better grade ceramic capacitor with a 50V rating, and at least  $10\mu F$  capacitance. The capacitor should be placed as close as possible to the device, while also minimizing the loop area formed by  $C_{IN}$  and the IN/GND pins.

When selecting an input capacitor, ensure that its voltage rating is at least 20% greater than the maximum voltage of the input supply. X5R or X7R dielectric types are the most often selected due to their small size, low cost, surge current capability, and high RMS current rating over a wide temperature and voltage range.

In situations where the input rail is supplied through long wires, it is recommended to add some bulk capacitance like electrolytic, tantalum or polymer type capacitors to reduce the overshoot and ringing caused by the added parasitic inductance.

Consider the RMS current rating of the input capacitor, paralleling additional capacitors if required to meet the calculated RMS ripple current.

$$I_{CIN\_RMS} = I_{OUT} \times \sqrt{D \times (1 - D)}$$

The worst-case condition occurs at  $D = 0.5$ , then

$$I_{CIN\_RMS,MAX} = \frac{I_{OUT}}{2}$$

For simplicity, use an input capacitor with an RMS current rating greater than 50% of the maximum load current. The

input capacitor value determines the input voltage ripple of the converter. If there is a voltage ripple requirement in the system, choose an appropriate input capacitor that meets the specification.

Given the very low ESR and ESL of ceramic capacitors, the input voltage ripple can be estimated using the formula:

$$V_{CIN\_RIPPLE,CAP} = \frac{I_{OUT}}{f_{SW} \times C_{IN}} \times D \times (1 - D)$$

The worst-case condition occurs at  $D = 0.5$ , then

$$V_{CIN\_RIPPLE,CAP,MAX} = \frac{I_{OUT}}{4 \times f_{SW} \times C_{IN}}$$

The capacitance value is less important than the RMS current rating. A single  $10\mu F$  X5R capacitor is sufficient for most applications.

### Output Inductor $L$

Consider the following when choosing this inductor:

- 1) Choose the inductance to provide a ripple current that is approximately 40% of the maximum output current. The recommended inductance is calculated as:

$$L = \frac{V_{OUT}(1 - V_{OUT} / V_{IN,MAX})}{f_{SW} \times I_{OUT,MAX} \times 0.4}$$

where  $f_{SW}$  is the switching frequency and  $I_{OUT,MAX}$  is the maximum load current.

The device has high tolerance for ripple current amplitude variation. As a result, the final choice of inductance can vary slightly from the calculated value with no significant performance impact.

- 2) For buck converter using FCCM light load operation mode, make sure the inductance value is high enough to avoid reverse current limit threshold is been triggered just under steady state if the load current is zero.
- 3) The inductor's saturation current rating must be greater than the peak inductor current under full load:

$$I_{SAT,MIN} > I_{OUT,MAX} + \frac{V_{OUT}(1 - V_{OUT}/V_{IN,MAX})}{2 \times f_{SW} \times L}$$

- 4) The DCR of the inductor and the core loss at the switching frequency must be low enough to achieve the desired efficiency requirement. Use an inductor with DCR less than  $20m\Omega$  to achieve good overall efficiency.

### Output Capacitor $C_{OUT}$

Select the output capacitor  $C_{OUT}$  to handle the output ripple requirements. Both steady state ripple and transient requirements must be taken into consideration when

selecting  $C_{OUT}$ . For the best performance, use a X5R or better grade ceramic capacitor with a 16V rating, and capacitance of at least  $10\mu\text{F}$ .

For applications where the design must meet stringent ripple requirements, the following considerations must be followed.

The output voltage ripple at the switching frequency is caused by the inductor current ripple ( $\Delta I_L$ ) on the output capacitor's ESR (ESR ripple), as well as the stored charge (capacitive ripple). When calculating total ripple, consider both.

$$V_{RIPPLE,ESR} = \Delta I_L \times ESR$$

$$V_{RIPPLE,CAP} = \frac{\Delta I_L}{8 \times C_{OUT} \times f_{SW}}$$

The measured capacitive ripple might be higher than the theoretical value because the effective capacitance for ceramic capacitors decreases with the voltage across its terminals. The voltage derating is usually included as a chart in the capacitor datasheet, and the ripple can be

recalculated after taking the target output voltage into account.

### Feedforward Capacitor $C_{FF}$

The device integrates the compensation components to achieve good stability and fast transient responses. In some applications, adding a ceramic capacitor (feedforward capacitor  $C_{FF}$ ) in parallel with  $R_H$  may further speed up the load transient response. Note that when the output LC parameter is large, the feedforward capacitor can be increased for providing sufficient ripple to FB for small output ripple and good transient behavior.

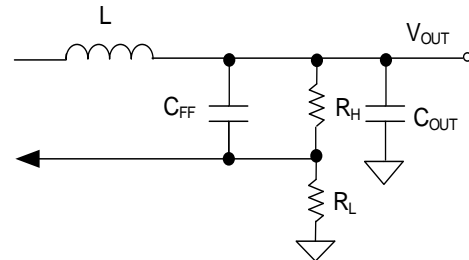
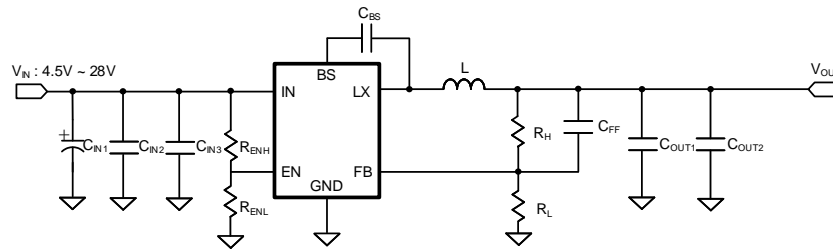
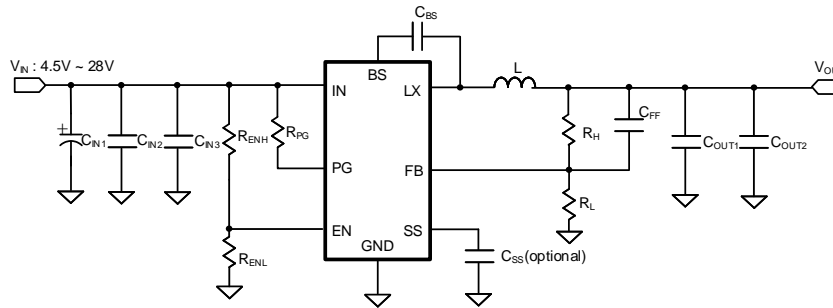


Figure7. Feedforward Network

## Application Schematic (SM8166/SM8166E, $V_{OUT} = 3.3V$ )



SM8166ADT/SM8166EADT



SM8166AIT/SM8166EAIT

Figure8. Schematic Diagram

## BOM List

Reference Designator	Description	Part Number	Manufacturer
C <sub>IN1</sub>	47 $\mu$ F/50V Electrolytic Capacitor		
C <sub>IN2</sub>	10 $\mu$ F/50V/X5R, 1206	GRM31CR61H106KA12L	m $\mu$ Rata
C <sub>IN3</sub> , C <sub>BS</sub>	0.1 $\mu$ F/50V/X5R, 0603	GRM188R61H104KA93D	m $\mu$ Rata
C <sub>OUT1</sub>	22 $\mu$ F/16V/X5R, 1206	GRM31CR61C226ME15L	m $\mu$ Rata
C <sub>OUT2</sub>	10 $\mu$ F/16V/X5R, 1206	GRM319R61C106KE15D	m $\mu$ Rata
C <sub>FF</sub>	100pF/50V/C0G,0603	GRM1885C1H101JA01D	m $\mu$ Rata
C <sub>SS</sub>	NC		
L	3.3 $\mu$ H/inductor, 7.3A	SPM6530T-3R3M	TDK
R <sub>H</sub> , R <sub>PG</sub>	100k $\Omega$ , 1%, 0603		
R <sub>L</sub>	22.1k $\Omega$ , 1%, 0603		
R <sub>ENH</sub>	10k $\Omega$ , 1%, 0603		
R <sub>ENL</sub>	1M $\Omega$ , 1%, 0603		

## Recommend Component Values for Typical Applications

V <sub>OUT</sub> (V)	R <sub>H</sub> (k $\Omega$ )	R <sub>L</sub> (k $\Omega$ )	C <sub>FF</sub> (pF)	L/Part Number	C <sub>OUT</sub>
1.2	100	100	10	2.2 $\mu$ H/SPM6530T-2R2M	1 $\times$ 22 $\mu$ F/16V/X5R, 1206 1 $\times$ 10 $\mu$ F/16V/X5R, 1206
1.8	100	49.9	47	2.2 $\mu$ H/SPM6530T-2R2M	1 $\times$ 22 $\mu$ F/16V/X5R, 1206 1 $\times$ 10 $\mu$ F/16V/X5R, 1206
3.3	100	22.1	100	3.3 $\mu$ H/SPM6530T-3R3M	1 $\times$ 22 $\mu$ F/16V/X5R, 1206 1 $\times$ 10 $\mu$ F/16V/X5R, 1206
5	100	13.7	220	4.7 $\mu$ H/PCMB104T-4R7	1 $\times$ 22 $\mu$ F/16V/X5R, 1206 1 $\times$ 10 $\mu$ F/16V/X5R, 1206

## Layout Design

Follow these PCB layout guidelines for optimal performance and thermal dissipation:

**Input Capacitors:** Place the input capacitors very close to IN and GND pins, minimizing the loop formed by these connections. The input capacitor should be connected to the IN and GND pins using a wide copper area.

**Output Capacitors:** Connect the  $C_{OUT}$  negative terminal to the GND pin using wide copper traces instead of vias, in order to achieve better accuracy and stability of the output voltage.

**Feedback Network:** Place the feedback components ( $R_H$ ,  $R_L$  and  $C_{FF}$ ) as close to the FB pin as possible. Avoid routing the feedback line near LX, or other high-frequency signals as it is noise-sensitive. Use a Kelvin connection to connect with  $C_{OUT}$  rather than the inductor output terminal.

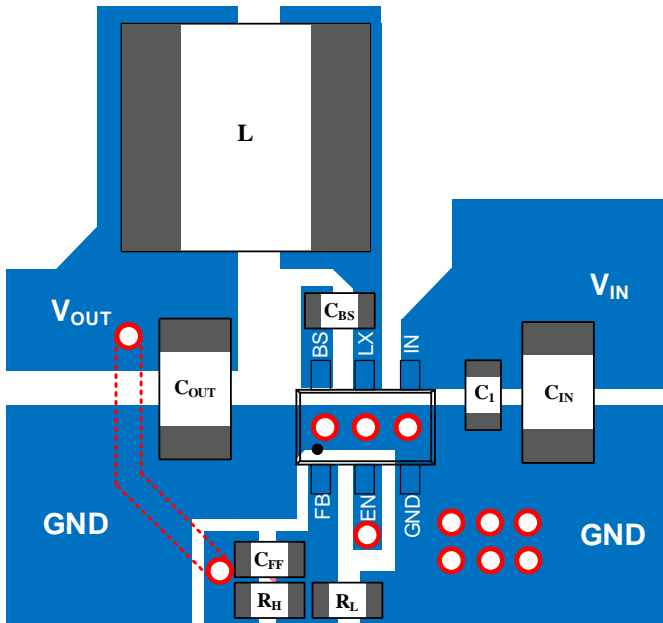
**LX Connection:** Keep the LX area small to prevent excessive EMI, while providing a wide copper trace to minimize parasitic resistance and inductance.

**BS Capacitor:** Place the BS capacitor on the **same** layer as the device, keep the BS voltage path (BS, LX and  $C_{BS}$ ) as short as possible.

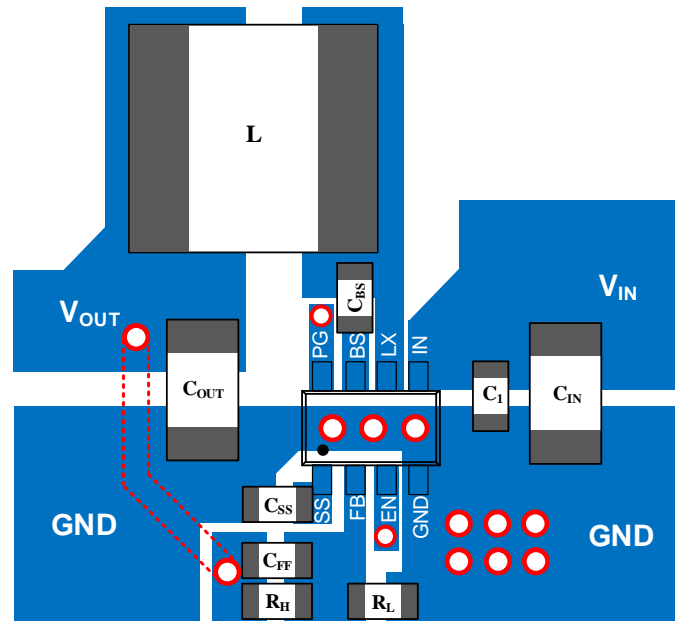
**EN Signal:** It is not recommended to connect EN pin directly to  $V_{IN}$  or another voltage source. A resistor in a range of  $1k\Omega$  to  $1M\Omega$  should be used if EN pin is pulled high.

**GND Vias:** Place an adequate number of vias on the GND layer around the device for better thermal performance. The exposed GND pad should be connected to a copper area larger than its size. Place multiple GND vias on it for heat dissipation.

**PCB Board:** To achieve the best thermal and noise performance, maximize the PCB copper area connecting to the GND pin. A ground plane is highly recommended if possible. Connect the ground pad to a large copper area to enhance thermal performance.



SM8166xADT

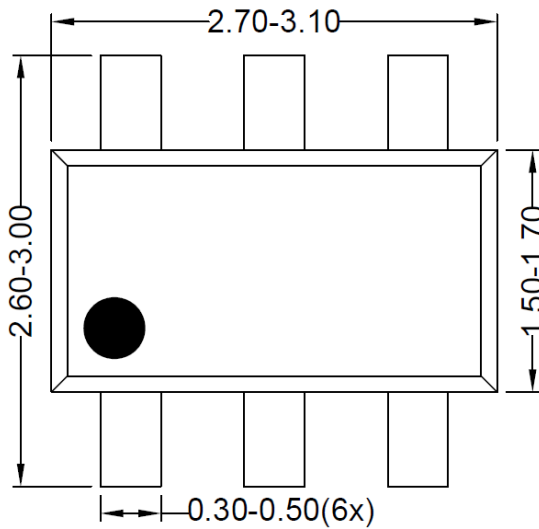


SM8166xAIT

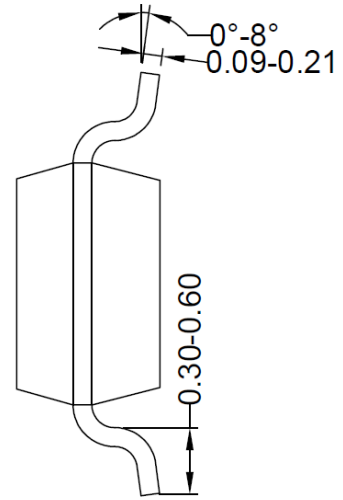
Figure9. Suggested PCB Layout

## Package Outline & PCB Layout

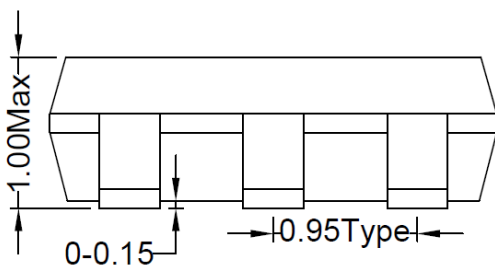
TSOT23-6



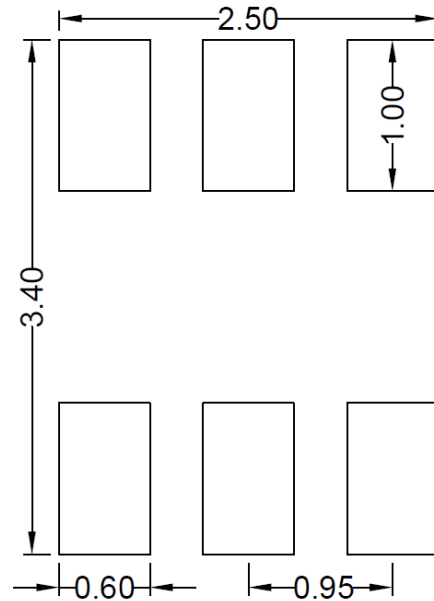
Top view



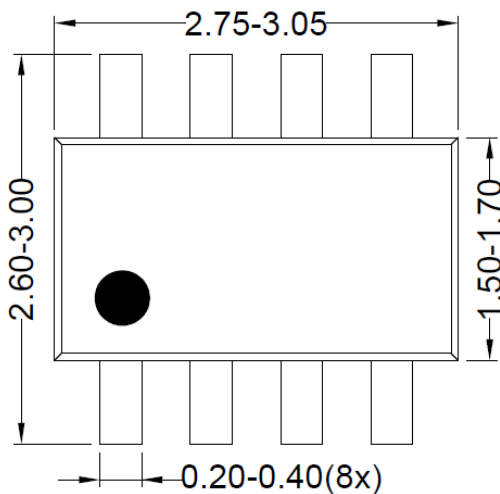
Side view



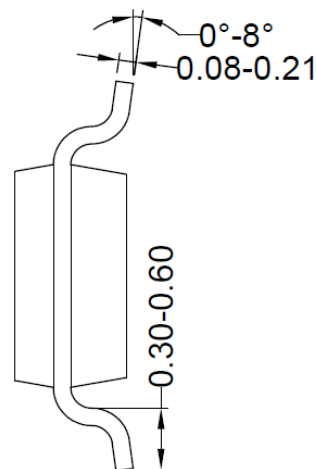
Front view



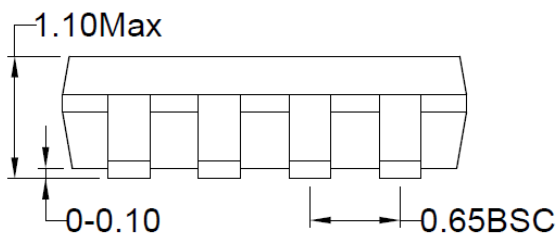
Recommended Pad Layout  
(Reference only)



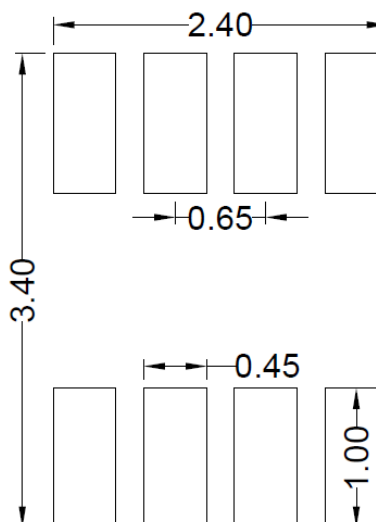
**Top view**



**Side view A**



**Side view B**



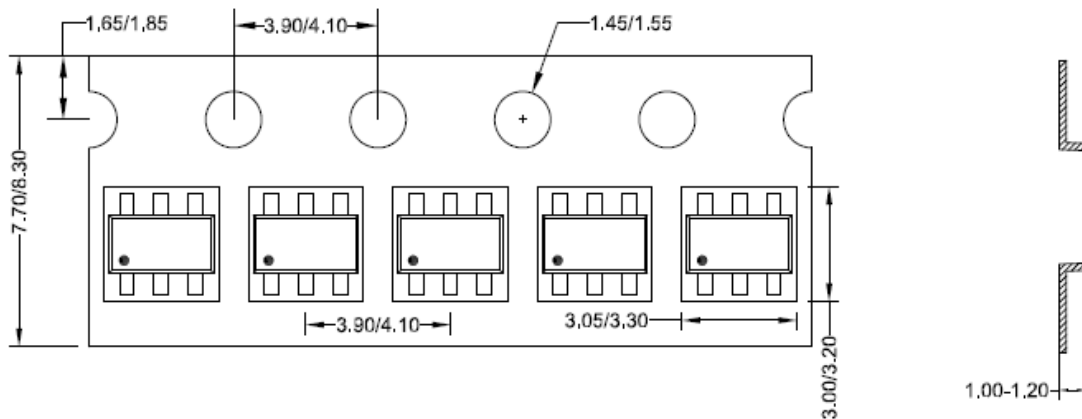
**Recommended PCB layout  
(Reference only)**

**Notes:** All dimension in millimeter and exclude mold flash & metal burr.

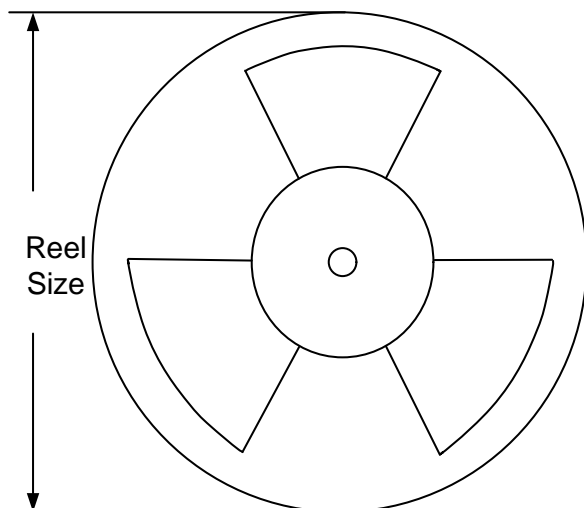
## Taping & Reel Specification

### TSOT23-6

#### 1. Taping orientation



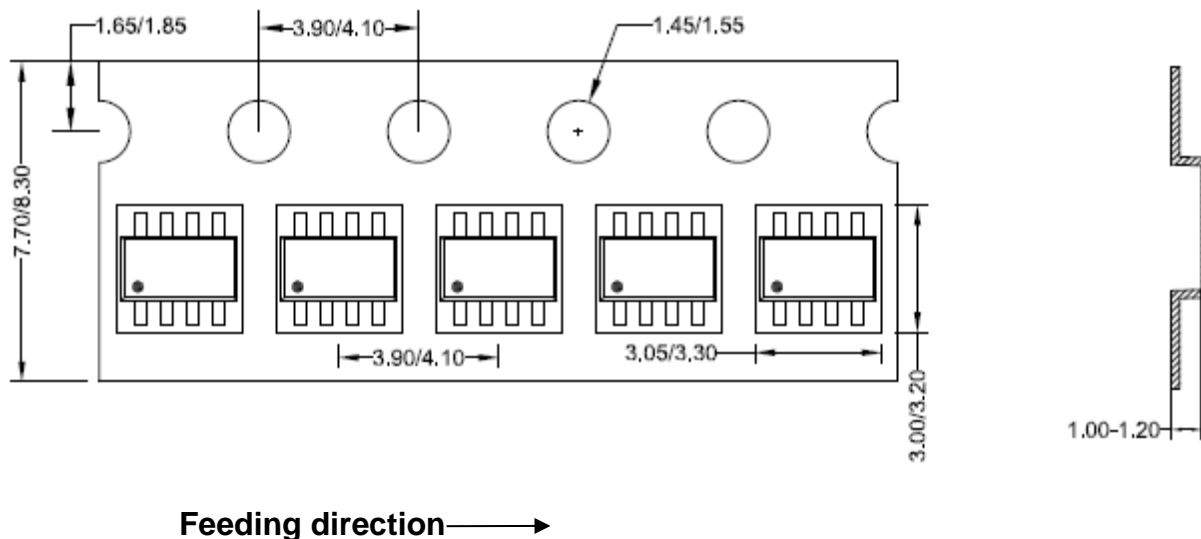
#### 2. Carrier Tape & Reel specification for packages



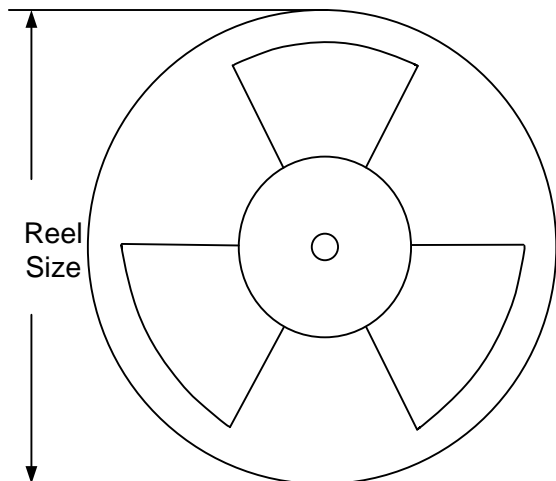
Package types	Tape width (mm)	Pocket pitch(mm)	Reel size (Inch)	Trailer length(mm)	Leader length (mm)	Qty per reel
TSOT23-6	8	4	7	400	160	3000

## TSOT23-8

### 1. Taping orientation



### 2. Carrier Tape & Reel specification for packages



Package type	Tape width (mm)	Pocket pitch(mm)	Reel size (Inch)	Trailer length(mm)	Leader length (mm)	Qty per reel
TSOT23-8	8	4	7	400	160	3000